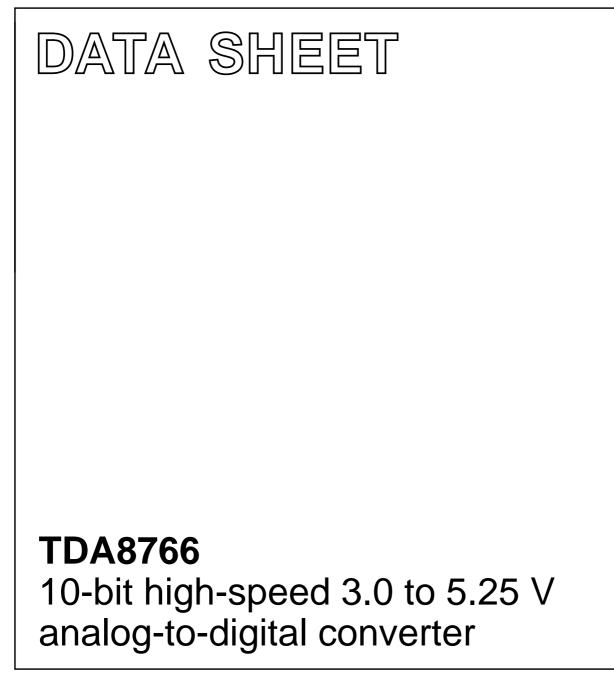
INTEGRATED CIRCUITS



Product specification Supersedes data of 1996 Mar 20 File under Integrated Circuits, IC02 2000 May 25



**TDA8766** 

## 10-bit high-speed 3.0 to 5.25 V analog-to-digital converter

### FEATURES

- 10-bit resolution
- 3.0 to 5.25 V operation
- Sampling rate up to 20 MHz
- DC sampling allowed
- High signal-to-noise ratio over a large analog input frequency range (9.3 effective bits at 1.0 MHz; full-scale input at f<sub>clk</sub> = 20 MHz)
- In-Range (IR) CMOS output
- CMOS/TTL compatible digital inputs and outputs
- External reference voltage regulator
- Power dissipation only 53 mW (typical value)
- Low analog input capacitance, no buffer amplifier required
- Standby mode
- No sample-and-hold circuit required.

### APPLICATIONS

High-speed analog-to-digital conversion for:

- Video data digitizing
- Camera
- Camcorder
- Radio communication.

### **GENERAL DESCRIPTION**

The TDA8766 is a 10-bit high-speed Analog-to-Digital Converter (ADC) for professional video and other applications. It converts with 3.0 to 5.25 V operation the analog input signal into 10-bit binary-coded digital words at a maximum sampling rate of 20 MHz. All digital inputs and outputs are CMOS compatible. A standby mode allows reduction of the device power consumption down to 4 mW.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>DDA</sub>	analog supply voltage		3.0	3.3	5.25	V
V <sub>DDD1</sub>	digital supply voltage 1		3.0	3.3	5.25	V
V <sub>DDD2</sub>	digital supply voltage 2		3.0	3.3	5.25	V
V <sub>DDO</sub>	output stages supply voltage		3.0	3.3	5.25	V
I <sub>DDA</sub>	analog supply current		_	7.5	10	mA
I <sub>DDD</sub>	digital supply current		-	7.5	10	mA
I <sub>DDO</sub>	output stages supply current	f <sub>clk</sub> = 20 MHz; C <sub>L</sub> = 20 pF; ramp input	-	1	2	mA
INL	integral non-linearity	f <sub>clk</sub> = 20 MHz; ramp input	_	±1	±2	LSB
DNL	differential non-linearity	f <sub>clk</sub> = 20 MHz; ramp input	-	±0.25	±0.7	LSB
f <sub>clk(max)</sub>	maximum clock frequency		20	-	_	MHz
P <sub>tot</sub>	total power dissipation	$V_{DDA} = V_{DDD} = V_{DDO} = 3.3 V$	-	53	73	mW

### **ORDERING INFORMATION**

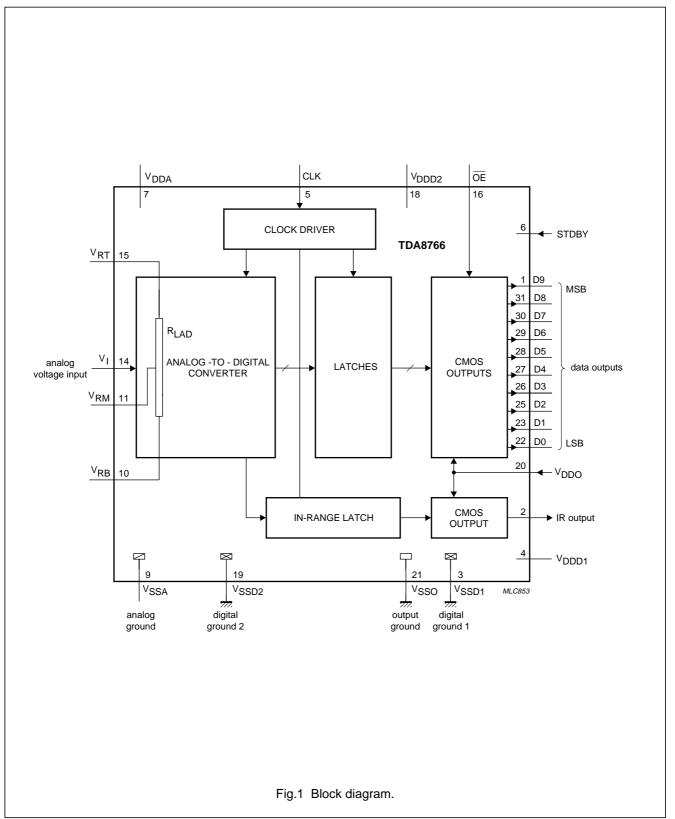
TYPE		PACKAGE						
NUMBER	NAME	DESCRIPTION	VERSION					
TDA8766G	LQFP32	plastic low profile quad flat package; 32 leads; body $5 \times 5 \times 1.4$ mm	SOT401-1					

### QUICK REFERENCE DATA

TDA8766

## 10-bit high-speed 3.0 to 5.25 V analog-to-digital converter

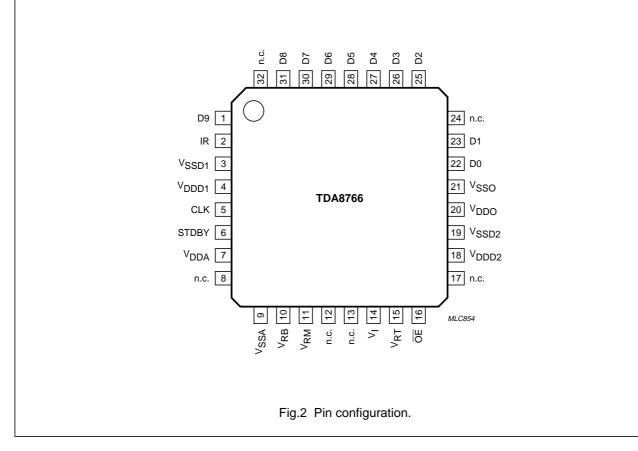
### **BLOCK DIAGRAM**



### PINNING

SYMBOL	PIN	DESCRIPTION
D9	1	data output; bit 9 (MSB)
IR	2	in-range data output
V <sub>SSD1</sub>	3	digital ground 1
V <sub>DDD1</sub>	4	digital supply voltage 1 (3.0 to 5.25 V)
CLK	5	clock input
STDBY	6	standby mode input
V <sub>DDA</sub>	7	analog supply voltage (3.0 to 5.25 V)
n.c.	8	not connected
V <sub>SSA</sub>	9	analog ground
V <sub>RB</sub>	10	reference voltage BOTTOM input
V <sub>RM</sub>	11	reference voltage MIDDLE input
n.c.	12	not connected
n.c.	13	not connected
VI	14	analog voltage input
V <sub>RT</sub>	15	reference voltage TOP input
ŌĒ	16	output enable input (active LOW)

SYMBOL	PIN	DESCRIPTION
n.c.	17	not connected
V <sub>DDD2</sub>	18	digital supply voltage 2 (3.0 to 5.25 V)
V <sub>SSD2</sub>	19	digital ground 2
V <sub>DDO</sub>	20	positive supply voltage for output stage (3.0 to 5.25 V)
V <sub>SSO</sub>	21	output stage ground
D0	22	data output; bit 0 (LSB)
D1	23	data output; bit 1
n.c.	24	not connected
D2	25	data output; bit 2
D3	26	data output; bit 3
D4	27	data output; bit 4
D5	28	data output; bit 5
D6	29	data output; bit 6
D7	30	data output; bit 7
D8	31	data output; bit 8
n.c.	32	not connected



### TDA8766

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>DDA</sub>	analog supply voltage	note 1	-0.3	+7.0	V
V <sub>DDD</sub>	digital supply voltage	note 1	-0.3	+7.0	V
V <sub>DDO</sub>	output stages supply voltage	note 1	-0.3	+7.0	V
$\Delta V_{DD}$	supply voltage difference				
	$V_{DDA} - V_{DDD}$		-1.0	+4.0	V
	V <sub>DDD</sub> – V <sub>DDO</sub>		-1.0	+4.0	V
	$V_{DDA} - V_{DDO}$		-1.0	+4.0	V
VI	input voltage	referenced to V <sub>SSA</sub>	-0.3	+7.0	V
V <sub>i(p-p)</sub>	AC input voltage for switching (peak-to-peak value)	referenced to V <sub>SSD</sub>	-	V <sub>DDD</sub>	V
I <sub>O</sub>	output current		-	10	mA
T <sub>stg</sub>	storage temperature		-55	+150	°C
T <sub>amb</sub>	ambient temperature		-20	+75	°C
Tj	junction temperature		_	150	°C

#### Note

1. The supply voltages  $V_{DDA}$ ,  $V_{DDD}$  and  $V_{DDO}$  may have any value between -0.3 and +7.0 V provided that the supply voltage differences  $\Delta V_{DD}$  are respected.

### HANDLING

Inputs and outputs are protected against electrostatic discharges in normal handling. However, to be totally safe, it is desirable to take normal precautions appropriate to handling integrated circuits.

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(jj-a)</sub>	thermal resistance from junction to ambient	in free air	90	K/W

### TDA8766

### CHARACTERISTICS

 $V_{DDA} = V_7 \text{ to } V_9 = 3.3 \text{ V}; V_{DDD} = V_4 \text{ to } V_3 = V_{18} \text{ to } V_{19} = 3.3 \text{ V}; V_{DDO} = V_{20} \text{ to } V_{21} = 3.3 \text{ V}; V_{SSA}, V_{SSD} \text{ and } V_{SSO} \text{ short-circuited together}; V_{i(p-p)} = 1.83 \text{ V}; C_L = 20 \text{ pF}; T_{amb} = 0 \text{ to } 70 \text{ }^{\circ}\text{C}; \text{ typical values measured at } T_{amb} = 25 \text{ }^{\circ}\text{C}; \text{ unless otherwise specified.}$ 

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Supplies						•
V <sub>DDA</sub>	analog supply voltage		3.0	3.3	5.25	V
V <sub>DDD1</sub>	digital supply voltage 1		3.0	3.3	5.25	V
V <sub>DDD2</sub>	digital supply voltage 2		3.0	3.3	5.25	V
V <sub>DDO</sub>	output stages supply voltage		3.0	3.3	5.25	V
$\Delta V_{DD}$	voltage difference					
	V <sub>DDA</sub> – V <sub>DDD</sub>		-0.2	-	+0.2	V
	V <sub>DDA</sub> – V <sub>DDO</sub>		-0.2	-	+2.25	V
	V <sub>DDD</sub> – V <sub>DDO</sub>		-0.2	-	+2.25	V
I <sub>DDA</sub>	analog supply current		-	7.5	10	mA
I <sub>DDD</sub>	digital supply current		_	7.5	10	mA
I <sub>DDO</sub>	output stages supply current	$f_{clk} = 20 \text{ MHz};$ ramp input; $C_L = 20 \text{ pF}$	-	1	2	mA
P <sub>tot</sub>	total power dissipation	operating; V <sub>DD</sub> = 3.3 V	-	53	73	mW
		standby mode	-	4	_	mW
Inputs						
CLOCK INPL	JT CLK (REFERENCED TO V <sub>SSD</sub> ); note	e 1				
V <sub>IL</sub>	LOW-level input voltage		0	_	0.3V <sub>DDD</sub>	V
VIH	HIGH-level input voltage	V <sub>DDD</sub> ≤ 3.6 V	0.6V <sub>DDD</sub>	_	V <sub>DDD</sub>	V
		V <sub>DDD</sub> = 3.3 V	0.7V <sub>DDD</sub>	_	V <sub>DDD</sub>	V
IIL	LOW-level input current	$V_{CLK} = 0.3 V_{DDD}$	-1	0	+1	μA
IIH	HIGH-level input current	$V_{CLK} = 0.7 V_{DDD}$	_	_	5	μA
Zi	input impedance	f <sub>clk</sub> = 20 MHz	-	4	_	kΩ
Ci	input capacitance	f <sub>clk</sub> = 20 MHz	-	3	_	pF
INPUTS OE	AND STDBY (REFERENCED TO VSSD	); see Tables 1 and 2				
VIL	LOW-level input voltage		0	_	0.3V <sub>DDD</sub>	V
V <sub>IH</sub>	HIGH-level input voltage	V <sub>DDD</sub> ≤ 3.6 V	0.6V <sub>DDD</sub>	-	V <sub>DDD</sub>	V
		V <sub>DDD</sub> = 3.3 V	0.7V <sub>DDD</sub>	_	V <sub>DDD</sub>	V
IIL	LOW-level input current	$V_{IL} = 0.3 V_{DDD}$	-1	_	_	μA
I <sub>IH</sub>	HIGH-level input current	$V_{IH} = 0.7 V_{DDD}$	-	-	1	μA
	PUT V <sub>I</sub> (REFERENCED TO V <sub>SSA</sub> )					
IIL	LOW-level input current	$V_{I} = V_{RB}$	_	0	_	μA
<u>I</u> IH	HIGH-level input current	$V_{I} = V_{RT}$	_	35	_	μΑ
Zi	input impedance	f <sub>i</sub> = 1 MHz	-	5	_	kΩ
Ci	input capacitance	f <sub>i</sub> = 1 MHz	_	8	_	pF

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Reference	voltages for resistor ladder; see	Table 3	-	4	-	•
V <sub>RB</sub>	reference voltage BOTTOM		1.1	1.2	_	V
V <sub>RT</sub>	reference voltage TOP		3.0	3.3	V <sub>DDA</sub>	V
V <sub>diff(ref)</sub>	differential reference voltage V <sub>RT</sub> – V <sub>RB</sub>		1.9	2.1	3.0	V
I <sub>ref</sub>	reference current		-	7.2	-	mA
R <sub>LAD</sub>	ladder resistance		-	290	_	Ω
TC <sub>RLAD</sub>	temperature coefficient of ladder resistance		-	539 1860	-	mΩ/K ppm
V <sub>offset(B)</sub>	offset voltage BOTTOM	note 2	_	135	_	mV
V <sub>offset(T)</sub>	offset voltage TOP	note 2	-	135	_	mV
V <sub>I(p-p)</sub>	analog input voltage (peak-to-peak value)	note 3	1.66	1.83	2.35	V
Outputs		1	,		•	•
DIGITAL OU	TPUTS D9 TO D0 AND IR (REFERENCE	р то V <sub>SSD</sub> )				
V <sub>OL</sub>	LOW-level output voltage	$I_0 = 1 \text{ mA}$	0	_	0.5	V
V <sub>OH</sub>	HIGH-level output voltage	$I_0 = -1 \text{ mA}$	V <sub>DDO</sub> - 0.5	_	V <sub>DDO</sub>	V
l <sub>oz</sub>	output current in 3-state mode	0.5 V < V <sub>O</sub> < V <sub>DDO</sub>	-20	_	+20	μA
Switching	characteristics	•	-	1	-	•
	JT CLK; see Fig.4; note 1					
f <sub>clk(max)</sub>	maximum clock frequency		20	_	_	MHz
t <sub>CPH</sub>	clock pulse width HIGH		15	_	_	ns
t <sub>CPL</sub>	clock pulse width LOW		15	_	_	ns
Analog sig	gnal processing (f <sub>clk</sub> = 20 MHz)	1	-			•
LINEARITY						
INL	integral non-linearity	ramp input; see Fig.6	-	±1	±2	LSB
DNL	differential non-linearity	ramp input; see Fig.7	_	±0.25	±0.7	LSB
INPUT SET I	RESPONSE; see Fig.8; note 4			1		
t <sub>STLH</sub>	analog input settling time LOW-to-HIGH	full-scale square wave	-	4	6	ns
t <sub>STHL</sub>	analog input settling time HIGH-to-LOW	full-scale square wave	-	4	6	ns
HARMONICS	5; see Fig.9; note 5					
THD	total harmonic distortion	f <sub>i</sub> = 1 MHz	-	-63	-	dB
SIGNAL-TO-	NOISE RATIO; see Fig.9; note 5	•	•			
S/N	signal-to-noise ratio (full-scale)	without harmonics; f <sub>i</sub> = 1 MHz	-	60	-	dB

### TDA8766

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
EFFECTIVE	BITS; see Fig.9; note 5				- <b>!</b>	
EB	effective bits	f <sub>i</sub> = 300 kHz	_	9.5	-	bits
		f <sub>i</sub> = 1 MHz	_	9.3	_	bits
		f <sub>i</sub> = 3.58 MHz	_	8.0	_	bits
Timing (f <sub>c</sub>	<b>.<sub>lk</sub> = 20 MHz; C<sub>L</sub> = 20 pF);</b> see Fig.4;	note 6	•	•	•	•
t <sub>ds</sub>	sampling delay time		_	-	5	ns
t <sub>h</sub>	output hold time		5	-	_	ns
t <sub>d</sub>	output delay time	V <sub>DDO</sub> = 4.75 V	8	12	15	ns
		V <sub>DDO</sub> = 3.15 V	8	17	20	ns
3-state ou	tput delay times; see Fig.5			,		•
t <sub>dZH</sub>	enable HIGH		_	14	18	ns
t <sub>dZL</sub>	enable LOW		_	16	20	ns
t <sub>dHZ</sub>	disable HIGH		_	16	20	ns
t <sub>dLZ</sub>	disable LOW		_	14	18	ns
Standby n	node output delay times			•		·
t <sub>d(stb)LH</sub>	standby LOW-to-HIGH transition		-	-	200	ns
t <sub>d(stb)HL</sub>	start-up HIGH-to-LOW transition		_	_	500	ns

#### Notes

- 1. In addition to a good layout of the digital and analog ground, it is recommended that the rise and fall times of the clock must not be less than 1 ns.
- 2. Analog input voltages producing code 0 up to and including 1023:
  - a)  $V_{offset(B)}$  (offset voltage BOTTOM) is the difference between the analog input which produces data equal to 00 and the reference voltage BOTTOM (V<sub>RB</sub>) at T<sub>amb</sub> = 25 °C.
  - b) V<sub>offset(T)</sub> (offset voltage TOP) is the difference between V<sub>RT</sub> (reference voltage TOP) and the analog input which produces data outputs equal to 1023 at T<sub>amb</sub> = 25 °C.
- In order to ensure the optimum linearity performance of such converter architecture, the lower and upper extremities
  of the converter reference resistor ladder (corresponding to output codes 0 and 1023 respectively) are connected to
  pins V<sub>RB</sub> and V<sub>RT</sub> via offset resistors R<sub>OB</sub> and R<sub>OT</sub> as shown in Fig.3.
  - a) The current flowing into the resistor ladder is  $I_L = \frac{V_{RT} V_{RB}}{R_{OB} + R_L + R_{OT}}$  and the full-scale input range at the converter,

to cover code 0 to code 1023, is 
$$V_{I} = R_{L} \times I_{L} = \frac{R_{L}}{R_{OB} + R_{L} + R_{OT}} \times (V_{RT} - V_{RB}) = 0.871 \times (V_{RT} - V_{RB})$$

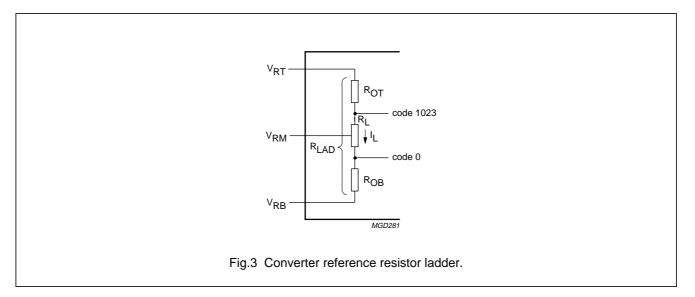
b) Since R<sub>L</sub>, R<sub>OB</sub> and R<sub>OT</sub> have similar behaviour with respect to process and temperature variation, the ratio

 $\frac{R_L}{R_{OB} + R_L + R_{OT}}$  will be kept reasonably constant from device to device. Consequently variation of the output

codes at a given input voltage depends mainly on the difference  $V_{RT} - V_{RB}$  and its variation with temperature and supply voltage. When several ADCs are connected in parallel and fed with the same reference source, the matching between each of them is then optimized.

4. The analog input settling time is the minimum time required for the input signal to be stabilized after a sharp full-scale input change (square-wave signal) in order to sample the signal and obtain correct output data.

- 5. Effective bits are obtained via a Fast Fourier Transform (FFT) treatment taking 8k acquisition points per equivalent fundamental period. The calculation takes into account all harmonics and noise up to half of the clock frequency (Nyquist frequency). Conversion to signal-to-noise ratio:  $S/N = EB \times 6.02 + 1.76 dB$ .
- 6. Output data acquisition: the output data is available after the maximum delay time of t<sub>d</sub>.



TDA8766

Table 1 Mode selection

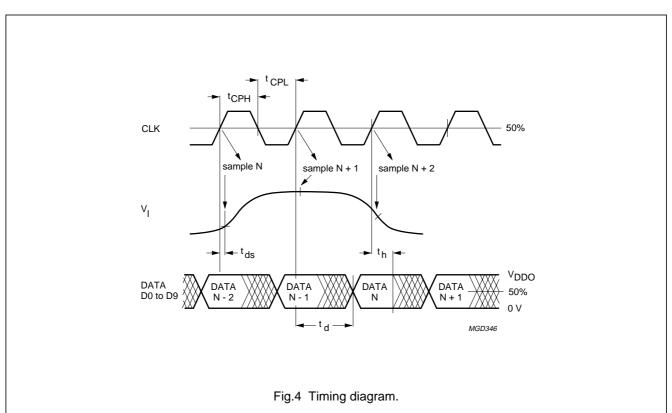
OE	D9 to D0	IR
1	high impedance	high impedance
0	active (binary)	active

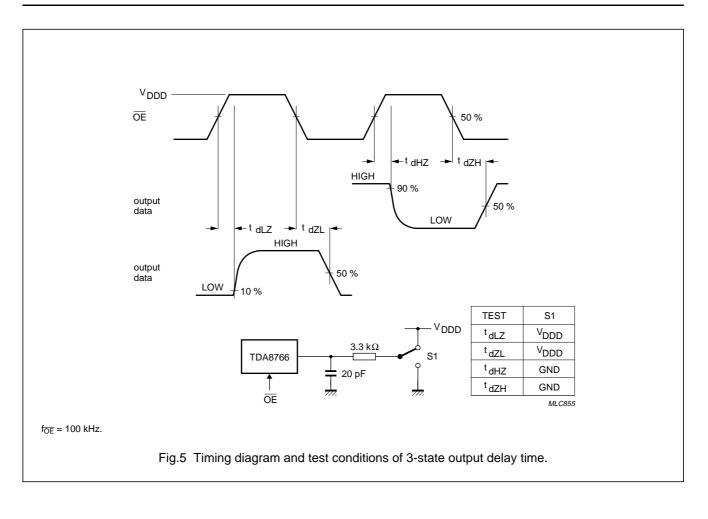
Table 2 Standby selection

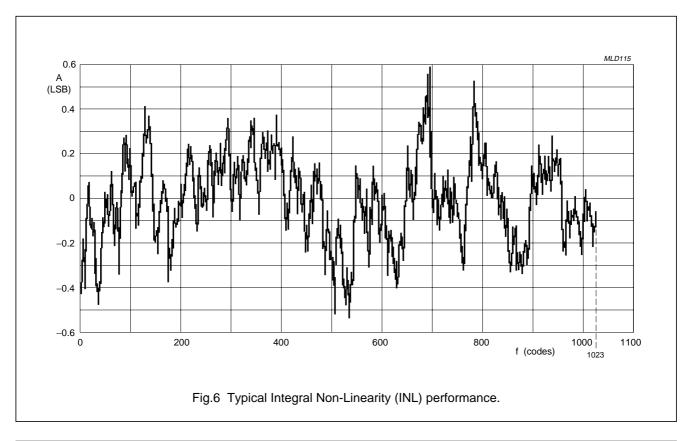
STDBY	D9 to D0	I <sub>DDA</sub> + I <sub>DDD</sub>		
1	last logic state	1.2 mA (typical value)		
0	active	15 mA (typical value)		

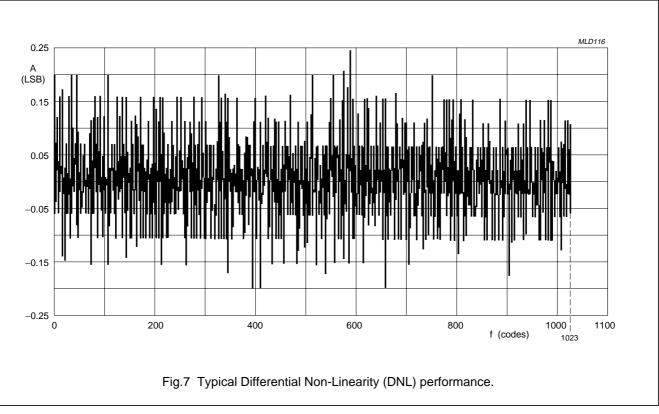
Table 3 Output coding and input voltage (typical values; referenced to V<sub>SSA</sub>)

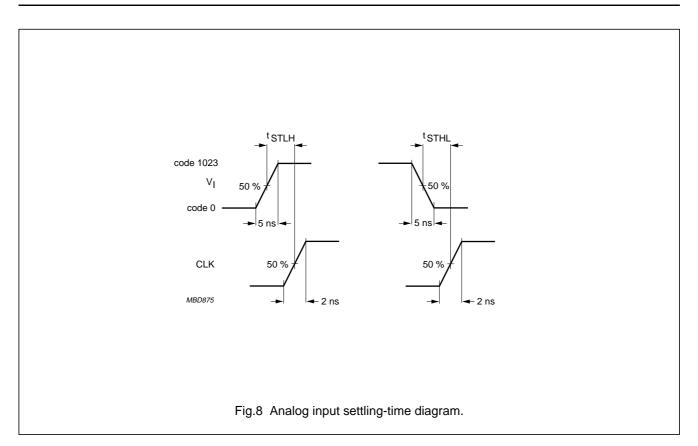
STEP	V	IR	BINARY OUTPUT BITS									
SIEF	V <sub>I(p-p)</sub>	IK	D9	D8	D7	D6	D5	D4	D3	D2	D1	D0
Underflow	<1.335 V	0	0	0	0	0	0	0	0	0	0	0
0	1.335 V	1	0	0	0	0	0	0	0	0	0	0
1	:	1	0	0	0	0	0	0	0	0	0	1
:	:	:	:	:	:	:	:	:	:	:	:	:
1022	:	1	1	1	1	1	1	1	1	1	1	0
1023	3.165 V	1	1	1	1	1	1	1	1	1	1	1
Overflow	>3.165 V	0	1	1	1	1	1	1	1	1	1	1

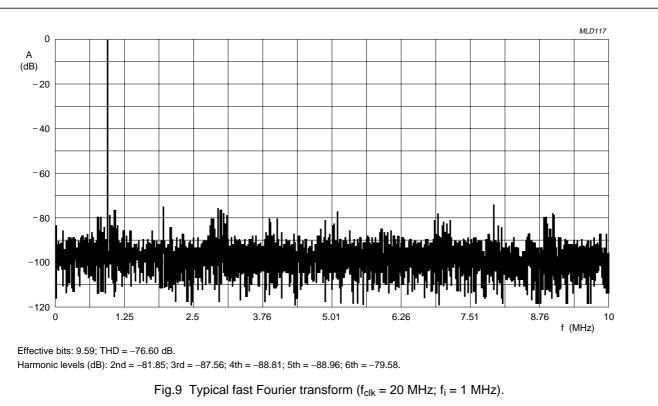






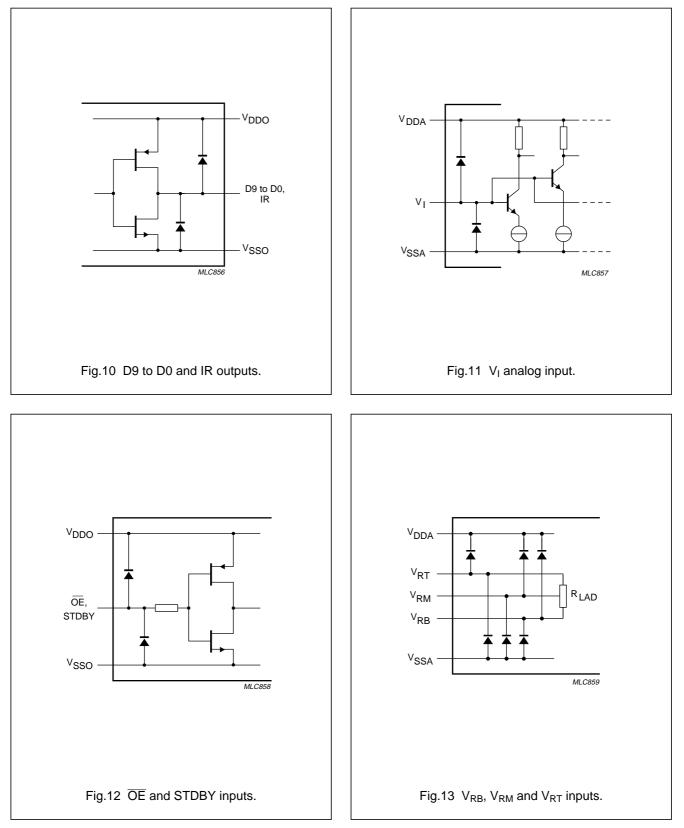


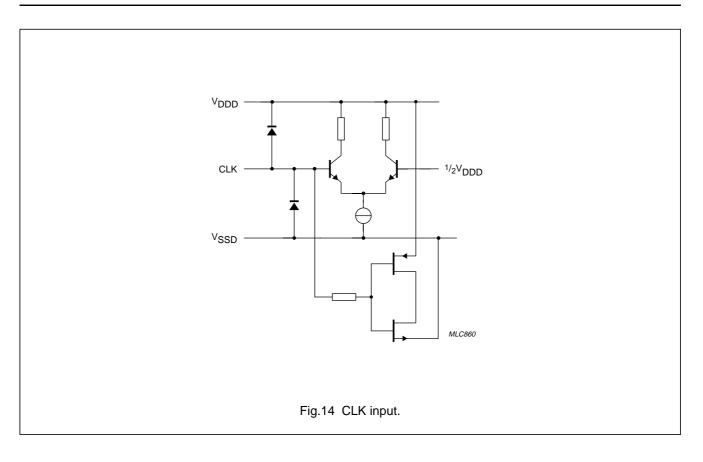




## TDA8766

### INTERNAL PIN CONFIGURATION



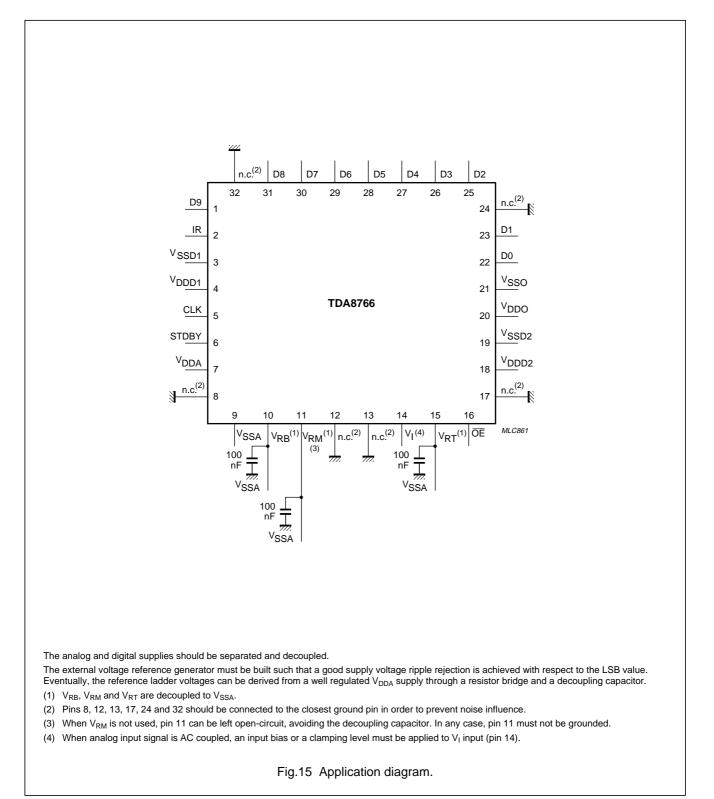


TDA8766

## 10-bit high-speed 3.0 to 5.25 V analog-to-digital converter

### **APPLICATION INFORMATION**

Additional application information will be supplied upon request (please quote number "AN96012").

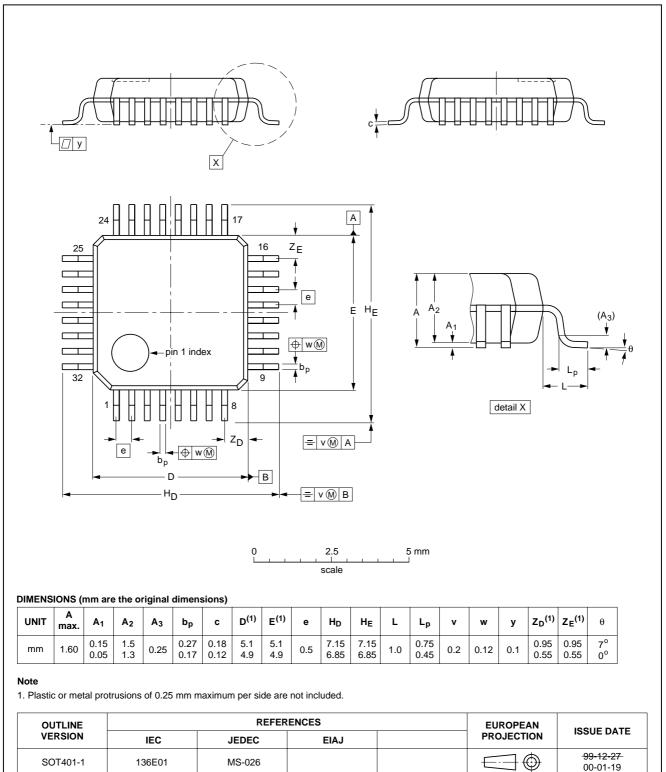


TDA8766

## 10-bit high-speed 3.0 to 5.25 V analog-to-digital converter

### PACKAGE OUTLINE

LQFP32: plastic low profile quad flat package; 32 leads; body 5 x 5 x 1.4 mm



SOT401-1

### SOLDERING

#### Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"Data Handbook IC26; Integrated Circuit Packages"* (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering is not always suitable for surface mount ICs, or for printed-circuit boards with high population densities. In these situations reflow soldering is often used.

#### **Reflow soldering**

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, infrared/convection heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferable be kept below 230 °C.

#### Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
  - larger than or equal to 1.27 mm, the footprint longitudinal axis is preferred to be parallel to the transport direction of the printed-circuit board;
  - smaller than 1.27 mm, the footprint longitudinal axis must be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

• For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C. A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

#### Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to  $300 \,^{\circ}$ C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320  $^\circ\text{C}.$ 

### TDA8766

### Suitability of surface mount IC packages for wave and reflow soldering methods

PACKAGE	SOLDERING METHOD	
FACKAGE	WAVE	REFLOW <sup>(1)</sup>
BGA, LFBGA, SQFP, TFBGA	not suitable	suitable
HBCC, HLQFP, HSQFP, HSOP, HTQFP, HTSSOP, SMS	not suitable <sup>(2)</sup>	suitable
PLCC <sup>(3)</sup> , SO, SOJ	suitable	suitable
LQFP, QFP, TQFP	not recommended <sup>(3)(4)</sup>	suitable
SSOP, TSSOP, VSO	not recommended <sup>(5)</sup>	suitable

#### Notes

- 1. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the "Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods".
- 2. These packages are not suitable for wave soldering as a solder joint between the printed-circuit board and heatsink (at bottom version) can not be achieved, and as solder may stick to the heatsink (on top version).
- 3. If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- 4. Wave soldering is only suitable for LQFP, TQFP and QFP packages with a pitch (e) equal to or larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- 5. Wave soldering is only suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

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### DATA SHEET STATUS

DATA SHEET STATUS	PRODUCT STATUS	DEFINITIONS (1)	
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.	
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.	
Product specification	Production	This data sheet contains final specifications. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.	

#### Note

1. Please consult the most recently issued data sheet before initiating or completing a design.

### DEFINITIONS

**Short-form specification** — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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